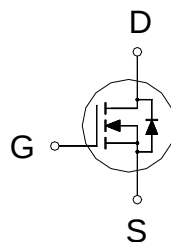


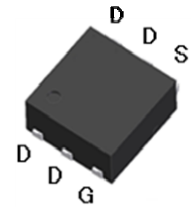
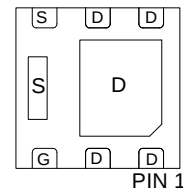
N-Channel Logic Level Enhancement Mode Field Effect Transistor

Product Summary:

BV _{DSS}	30V
R _{DS(on)} (MAX.)	15mΩ
I _D	8A



Bottom View



UIS, R_g 100% Tested

Pb-Free Lead Plating & Halogen Free



ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNIT
Gate-Source Voltage		V _{GS}	±20	V
Continuous Drain Current	T _A = 25 °C	I _D	8	A
	T _A = 100 °C		6	
Pulsed Drain Current ¹		I _{DM}	32	
Avalanche Current		I _{AS}	10	mJ
Avalanche Energy	L = 0.1mH, I _D =10A, R _G =25Ω	E _{AS}	5	
Repetitive Avalanche Energy ²	L = 0.05mH	E _{AR}	2.5	
Power Dissipation	T _A = 25 °C	P _D	2.08	W
	T _A = 100 °C		0.83	
Operating Junction & Storage Temperature Range		T _j , T _{stg}	-55 to 150	°C

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNIT
Junction-to-Case	R _{θJC}		12	°C / W
Junction-to-Ambient ³	R _{θJA}		60	

¹Pulse width limited by maximum junction temperature.

²Duty cycle ≤ 1%

³60°C / W when mounted on a 1 in² pad of 2 oz copper.

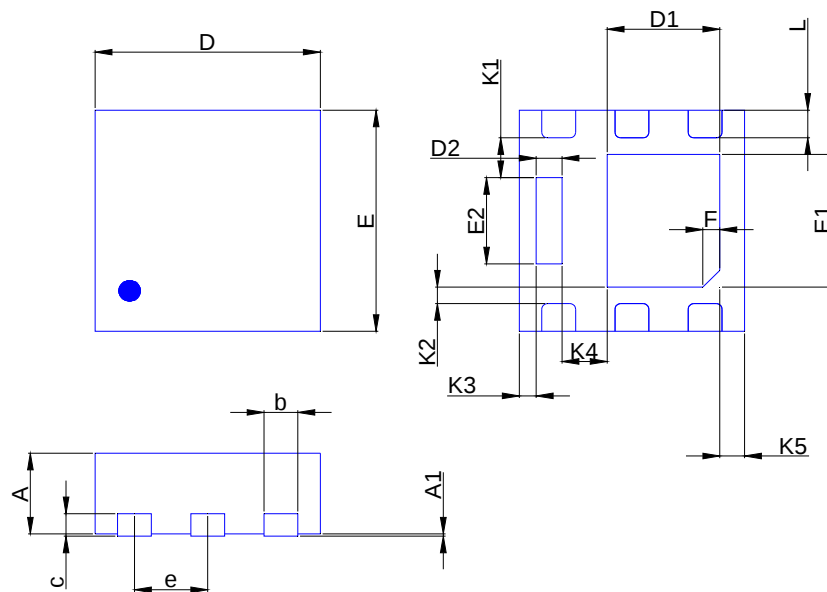
ELECTRICAL CHARACTERISTICS (T_A = 25 °C, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	30			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	1	1.5	3	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0V, V _{GS} = ±20V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 24V, V _{GS} = 0V			1	μA
		V _{DS} = 20V, V _{GS} = 0V, T _J = 125 °C			25	
On-State Drain Current ¹	I _{D(ON)}	V _{DS} = 10V, V _{GS} = 10V	8			A
Drain-Source On-State Resistance ¹	R _{DS(ON)}	V _{GS} = 10V, I _D = 8A		12	15	mΩ
		V _{GS} = 4.5V, I _D = 5A		18	24	
Forward Transconductance ¹	g _{fs}	V _{DS} = 5V, I _D = 8A		18		S
DYNAMIC						
Input Capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = 15V, f = 1MHz		597		pF
Output Capacitance	C _{oss}			111		
Reverse Transfer Capacitance	C _{rss}			96		
Gate Resistance	R _g	V _{GS} = 15mV, V _{DS} = 0V, f = 1MHz		2.0		Ω
Total Gate Charge ^{1,2}	Q _g (V _{GS} =10V)	V _{DS} = 15V, V _{GS} = 10V, I _D = 8A		13.3		nC
	Q _g (V _{GS} =4.5V)			7.0		
Gate-Source Charge ^{1,2}	Q _{gs}			2.2		
Gate-Drain Charge ^{1,2}	Q _{gd}			3.9		
Turn-On Delay Time ^{1,2}	t _{d(on)}	V _{DS} = 15V, I _D = 1A, V _{GS} = 10V, R _{GS} = 6Ω		10		nS
Rise Time ^{1,2}	t _r			8		
Turn-Off Delay Time ^{1,2}	t _{d(off)}			20		
Fall Time ^{1,2}	t _f			10		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T _c = 25 °C)						
Continuous Current	I _S				8	A
Pulsed Current ³	I _{SM}				32	
Forward Voltage ¹	V _{SD}	I _F = I _S , V _{GS} = 0V			1.2	V
Reverse Recovery Time	t _{rr}	I _F = I _S , dI _F /dt = 100A / μS		15		nS
Reverse Recovery Charge	Q _{rr}			12		nC

¹Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.

³Pulse width limited by maximum junction temperature.

Device Name: LB15N03A for EDFN 2 x 2



Dimension in mm

Dimension	A	A1	b	c	D	D1	D2	E	E1	E2	e	F	f	K1	K2	L	K3	K4	K5
Min.	0.70	0.00	0.25		1.9	0.9	0.13	1.9	1.1	0.68				0.306	0.10	0.2	0.10	0.35	0.17
Typ.	0.75	0.02	0.30	0.203	2.0	1.0	0.23	2.0	1.2	0.78	0.65	0.15	45°	0.356	0.15	0.25	0.15	0.40	0.22
Max.	0.80	0.05	0.35		2.1	1.1	0.33	2.1	1.3	0.88				0.406	0.20	0.3	0.20	0.45	0.27

